

## 1. Global joint venture starts operations as WeEn Semiconductors

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WeEn Semiconductors



**Product data sheet** 

## 1. General description

Planar passivated high commutation three quadrant triac in a SOT78 (TO-220AB) plastic package. This "series D" triac balances the requirements of commutation performance and gate sensitivity. The "very sensitive gate" "series D" is intended for interfacing with low power drivers including microcontrollers.

## 2. Features and benefits

- 3Q technology for improved noise immunity
- Direct interfacing with low power drivers and microcontrollers
- Good immunity to false turn-on by dV/dt
- High commutation capability with very sensitive gate
- High voltage capability
- Planar passivated for voltage ruggedness and reliability
- Triggering in three quadrants only
- · Very sensitive gate for easy logic level triggering

# 3. Applications

- Electronic thermostats (heating and cooling)
- · High power motor controls e.g. washing machines and vacuum cleaners

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	600	V
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	-	100	Α
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 100 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	-	12	Α
Static characte	eristics					,
I <sub>GT</sub>	gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 7$	-	-	5	mA
		$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA





**3Q Hi-Com Triac** 

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-;	-	-	5	mA
		T <sub>j</sub> = 25 °C; <u>Fig. 7</u>				

# 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	T1	main terminal 1	mb	T2—T1
2	T2	main terminal 2	<del>                                     </del>	Sym051
3	G	gate		·
mb	T2	mounting base; main terminal 2		
			TO-220AB (SOT78)	

# 6. Ordering information

Table 3. Ordering information

Table 0. Ordering membrane						
Type number	Package					
	Name	Description	Version			
BTA312-600D	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			
BTA312-600D/DG	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78			

**3Q Hi-Com Triac** 

# 7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DRM}$	repetitive peak off-state voltage		-	600	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{mb} \le 100 ^{\circ}\text{C}$ ; Fig. 1; Fig. 2; Fig. 3	-	12	А
I <sub>TSM</sub>	non-repetitive peak on-state current	full sine wave; $T_{j(init)} = 25 \text{ °C}$ ; $t_p = 20 \text{ ms}$ ; Fig. 4; Fig. 5	-	100	А
		full sine wave; $T_{j(init)} = 25 ^{\circ}C$ ; $t_p = 16.7  \text{ms}$	-	110	А
I <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	50	A <sup>2</sup> s
dl <sub>T</sub> /dt	rate of rise of on-state current	$I_T = 20 \text{ A}; I_G = 0.2 \text{ A}; dI_G/dt = 0.2 \text{ A/}\mu\text{s}$	-	100	A/µs
I <sub>GM</sub>	peak gate current		-	2	Α
$P_GM$	peak gate power		-	5	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.5	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C

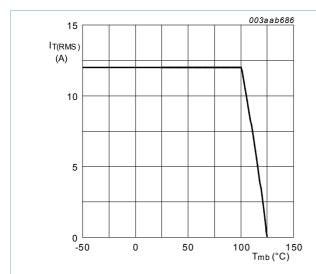
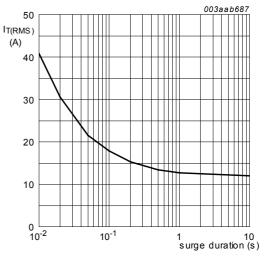


Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values



 $f = 50 \text{ Hz}; T_{mb} = 100 \,^{\circ}\text{C}$ 

Fig. 2. RMS on-state current as a function of surge duration; maximum values

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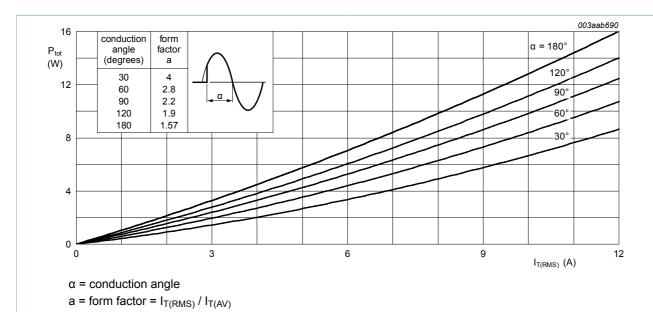


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

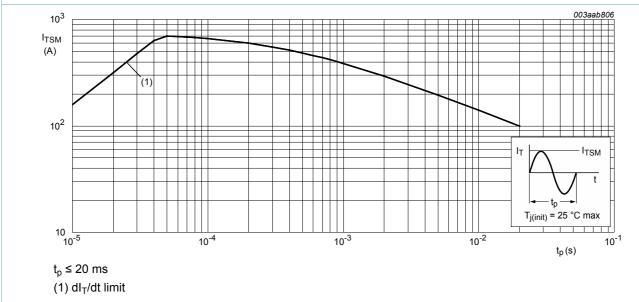


Fig. 4. Non-repetitive peak on-state current as a function of pulse duration; maximum values

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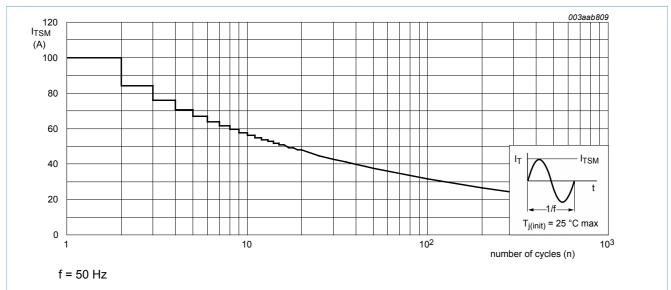


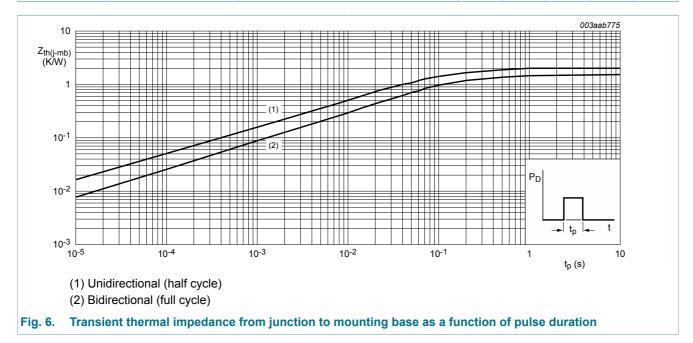
Fig. 5. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

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## 8. Thermal characteristics

Table 5. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-mb)</sub>	thermal resistance	full cycle; Fig. 6	-	-	1.5	K/W
	from junction to mounting base	half cycle; Fig. 6	-	-	2	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	-	60	-	K/W

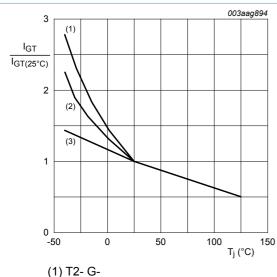


## 9. Characteristics

#### Table 6. Characteristics

Parameter	Conditions	Min	Тур	Max	Unit
acteristics				·	
gate trigger current	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; \frac{\text{Fig. 7}}{}$	-	-	5	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + \text{ G-;}$ $T_j = 25 \text{ °C; } \frac{\text{Fig. 7}}{}$	-	-	5	mA
	$V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2-\text{ G-;}$ $T_j = 25 \text{ °C; } Fig. 7$	-	-	5	mA
latching current	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	10	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$ $T_j = 25 \text{ °C}; Fig. 8$	-	-	15	mA
	$V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; \text{ T2- G-};$ $T_j = 25 \text{ °C}; \underline{\text{Fig. 8}}$	-	-	15	mA
holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	10	mA
on-state voltage	I <sub>T</sub> = 15 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
gate trigger voltage	$V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$ Fig. 11	-	0.8	1	V
	$V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$ Fig. 11	0.25	0.4	-	V
off-state current	V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C	-	0.1	0.5	mA
naracteristics		'		•	
rate of rise of off-state voltage	$V_{DM}$ = 402 V; $T_j$ = 125 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit	20	-	-	V/µs
rate of change of commutating current	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 20 V/ $\mu$ s; (snubberless condition); gate open circuit	1	-	-	A/ms
	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 10 V/ $\mu$ s; gate open circuit	1.5	-	-	A/ms
	$V_D$ = 400 V; $T_j$ = 125 °C; $I_{T(RMS)}$ = 12 A; $dV_{com}/dt$ = 1 V/ $\mu$ s; gate open circuit	4.5	-	-	A/ms
	gate trigger current  latching current  holding current  on-state voltage gate trigger voltage  off-state current  haracteristics  rate of rise of off-state voltage  rate of change of				

**3Q Hi-Com Triac** 



- (2) T2+ G-
- (3) T2+ G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

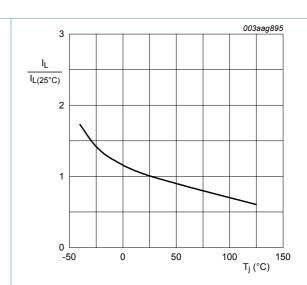


Fig. 8. Normalized latching current as a function of junction temperature

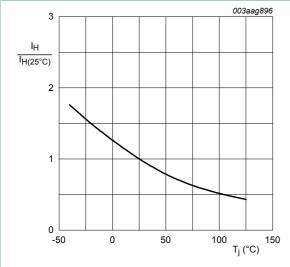
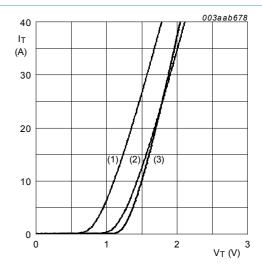


Fig. 9. Normalized holding current as a function of junction temperature



 $V_o = 1.164 \text{ V}; R_s = 0.027 \Omega$ 

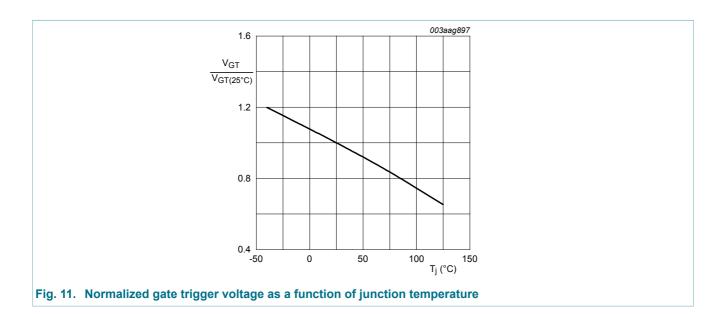
(1) T<sub>j</sub> = 125 °C; typical values

(2) T<sub>i</sub> = 125 °C; maximum values

(3) T<sub>i</sub> = 25 °C; maximum values

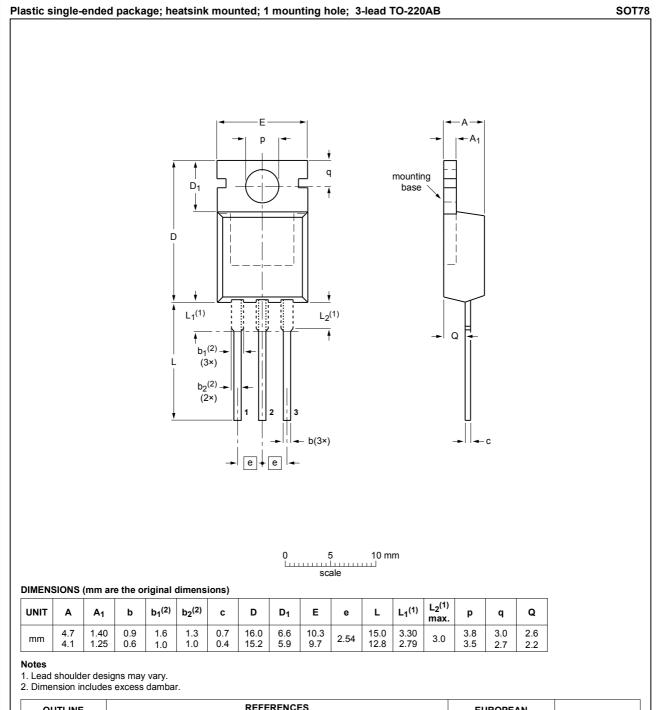
Fig. 10. On-state current as a function of on-state voltage

**3Q Hi-Com Triac** 



9/13

# 10. Package outline



OUTLINE		REFER	ENCES	EUROPEAN ISSUE DAT	
VERSION	IEC	JEDEC	JEITA	PROJECTION	1330E DATE
SOT78		3-lead TO-220AB	SC-46		<del>08-04-23</del> 08-06-13

Fig. 12. Package outline TO-220AB (SOT78)

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# 12. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Limiting values	3
8	Thermal characteristics	6
9	Characteristics	7
10	Package outline	10
11	Legal information	11
11.1	Data sheet status	11
11.2	Definitions	11
11.3	Disclaimers	11
11.4	Trademarks	12

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13 / 13